









# **CET6836**

#### 60V ▲ 85mΩ ▲ 4A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

SOT223 package ▲ MSL 3

Super high dense cell density for extremely low R<sub>DS(ON)</sub>

Rugged and reliable

## **MAXIMUM RATINGS**

Parameter (T <sub>A</sub> = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	60V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current	I <sub>D</sub>	4A
Pulsed Drain Current Note 1	I <sub>DM</sub>	16A
Maximum Power Dissipation	P <sub>D</sub>	3W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

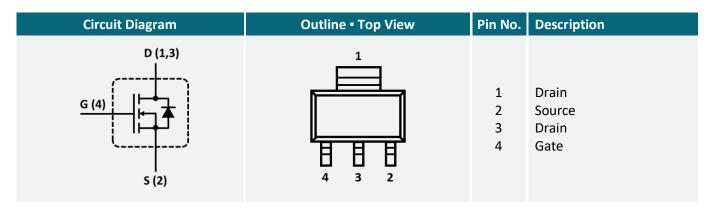
#### THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case Note 2	R <sub>TH_JC</sub>	42°C/W

## **APPLICATIONS**

DC/DC			ower tches
	(S)	SWI	cries
	Converter	Converter Fan	Converter Fan Control Swi

### **PIN DESCRIPTION**





## **ELECTRICAL CHARACTERISTICS** ▲ T<sub>A</sub> = 25°C, unless otherwise noted

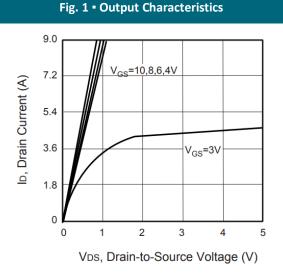
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 250\mu A$	$BV_{DSS}$	60			V
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	$I_{GSSF}$			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	$I_{GSSR}$			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	$V_{GS(th)}$	1		3	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 2A$	R <sub>DS(ON)</sub>		85	102	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 5V$ , $I_D = 1A$	R <sub>DS(ON)</sub>		97	126	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	C <sub>ISS</sub>		405		pF
Output Capacitance	$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	Coss		70		pF
Reverse Transfer Capacitance	$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$ $C_{RSS}$			30		pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{DD}$ = 30V, $V_{GS}$ = 10V, $I_{D}$ = 1.5A, $R_{G(ext)}$ = 3 $\Omega$	t <sub>D(ON)</sub>		7		ns
Turn-On Rise Time	$V_{DD}$ = 30V, $V_{GS}$ = 10V, $I_D$ = 1.5A, $R_{G(ext)}$ = 3 $\Omega$	t <sub>R</sub>		2.7		ns
Turn-Off Delay Time	$V_{DD}$ = 30V, $V_{GS}$ = 10V, $I_D$ = 1.5A, $R_{G(ext)}$ = 3 $\Omega$	t <sub>D(OFF)</sub>		18.8		ns
Turn-Off Fall Time	$V_{DD}$ = 30V, $V_{GS}$ = 10V, $I_D$ = 1.5A, $R_{G(ext)}$ = 3 $\Omega$	t <sub>F</sub>		1.6		ns
Total Gate Charge	$V_{DS}$ = 30V, $V_{GS}$ = 4.5V, $I_{D}$ = 2.5A	$Q_{G}$		3.6		nC
Gate Source Charge	$V_{DS}$ = 30V, $V_{GS}$ = 4.5V, $I_{D}$ = 2.5A	Q <sub>GS</sub>		0.8		nC
Gate Drain Charge	$V_{DS} = 30V$ , $V_{GS} = 4.5V$ , $I_D = 2.5A$	$Q_{GD}$		1.6		nC
<b>Drain-Source Diode Characteristics a</b>	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 3		Is			2.5	Α
Drain-Source Diode Forward Voltage Note 3	$V_{GS} = 0V$ , $I_S = 1A$	$V_{SD}$			1.2	V

#### Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, t ≤ 10 sec
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.

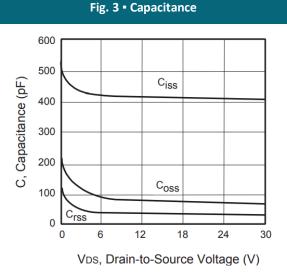


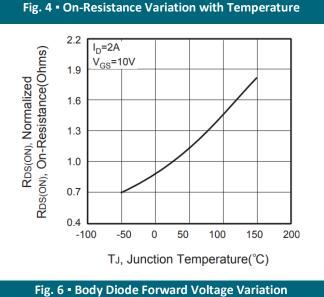
#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

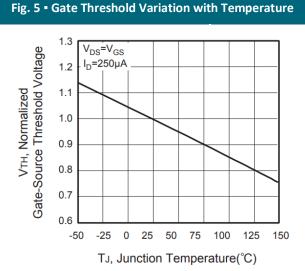


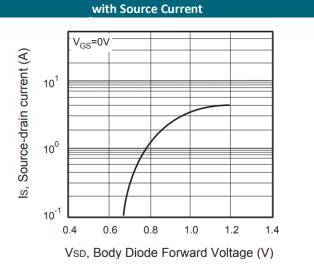
Yes, Gate-to-Source Voltage (V)

Fig. 2 • Transfer Characteristics









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#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

#### Fig. 7 • Gate Charge

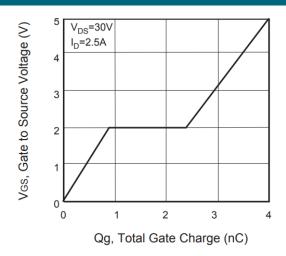


Fig. 8 • Maximum Safe Operating Area

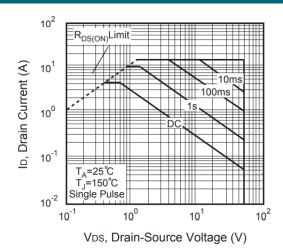
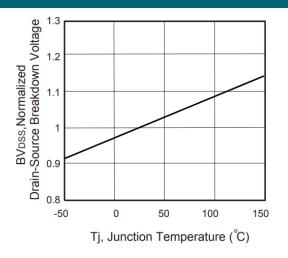


Fig. 9 • Breakdown Voltage Variation vs. Temperature





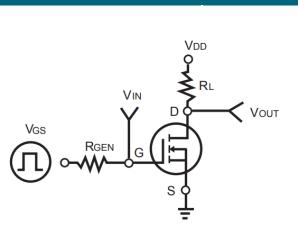
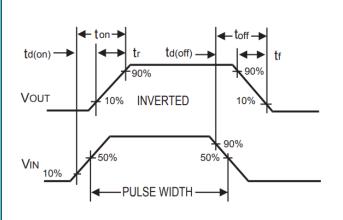


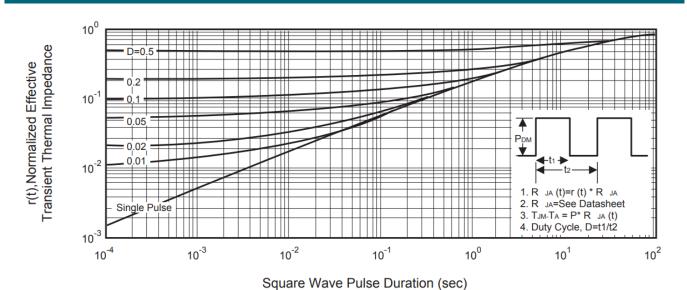
Fig. 11 • Switching Waveforms



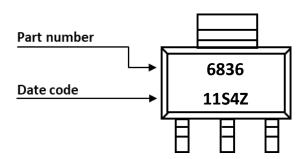


#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve



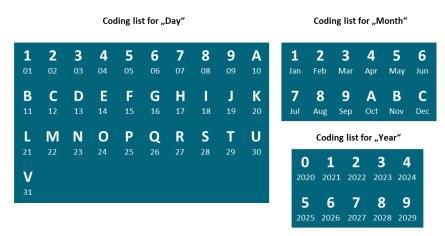
## **PART MARKING**



#### **DATE CODE**

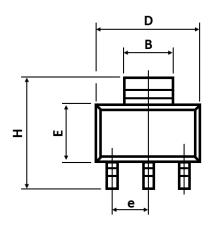
Example: 11S4Z

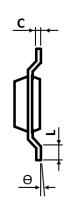


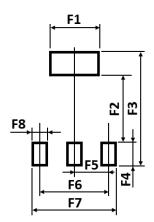


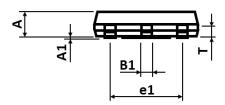


## PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
Α	1.500	-	1.700	
A1	0.020	-	0.100	
В	2.950	-	3.200	
B1	0.670	-	0.800	
С	0.240	-	0.350	
D	6.300	-	6.850	
e		2 300 TYP		

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)			
e1		4.600 TYP				
E	3.300	-	3.800			
Н	6.700	-	7.300			
L	0.900	-	-			
Т	0.600	-	0.800			
θ	10° MAX					

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	3.500	-
F2	-	4.600	-
F3	-	8.000	
F4	-	1.600	

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.300	-
F6	-	4.600	-
F7	-	5.600	-
F8	-	1.200	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

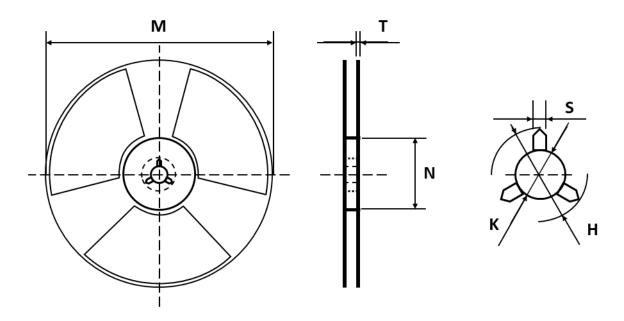
2. For further information, please reference document IPC-7351A.

## **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CET6836	SOT223	7" Reel	2,500pcs	5,000pcs	15,000pcs

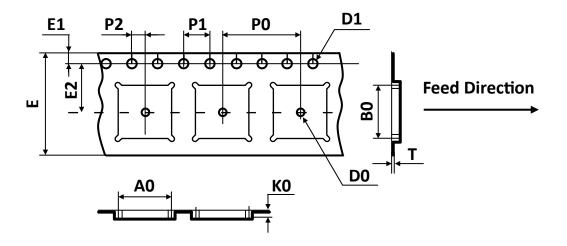


## **REEL DIMENSIONS** ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	K	S
Q <sub>mam</sub>	Ø180	Ø178.00	Ø54.00	1.20	20.00	13.30	3.00
8mm	0100	±1.00	±0.50	±0.20	±1.00	±0.30	±1.00

## **TAPE DIMENSIONS** ▲ All dimensions in mm

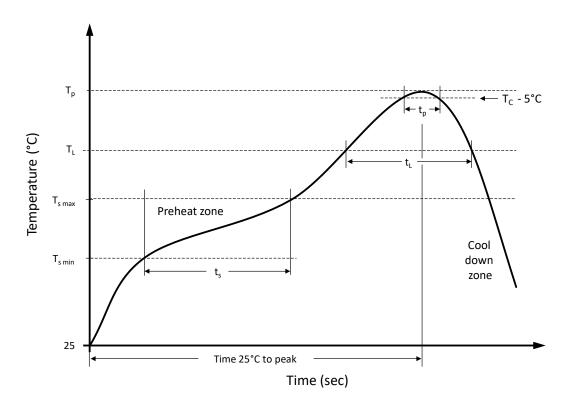


Package	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	T
SOT223	2.40	2.60	1.20	1.00	1.50	8.00	1.75	3.50	4.00	4.00	2.00	0.20
301223	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



## RECOMMENDED REFLOW SOLDERING PROFILE



## **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T <sub>s max</sub>	150 °C	200 °C
Preheat time t <sub>s</sub> from T <sub>s min</sub> to T <sub>s max</sub>	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	$T_L$	183 °C	217 °C
Time t <sub>L</sub> maintained above T <sub>L</sub>	t <sub>L</sub>	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate (T <sub>L</sub> to T <sub>p</sub> )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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